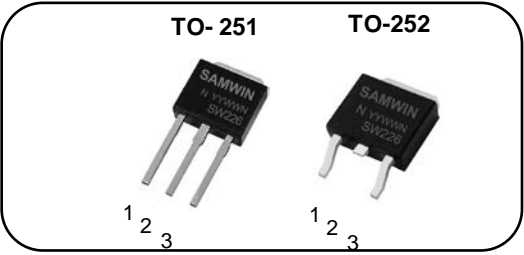


N-channel Enhanced mode TO-251/TO-252 MOSFET

Features

- High ruggedness
- Low  $R_{DS(ON)}$  (Typ1.83Ω)@ $V_{GS}=10V$
- Low Gate Charge (Typ30 nC)
- Improved dv/dt Capability
- 100% Avalanche Tested
- Application:Charge,Adaptor,LED



1. Gate 2. Drain 3. Source

**$BV_{DSS}$  : 600V**  
 **$I_D$  : 4.0A**  
 **$R_{DS(ON)}$  : 1.83Ω**



General Description

This power MOSFET is produced with advanced technology of SAMWIN. This technology enable the power MOSFET to have better characteristics, including fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW I 226N	SW226N	TO-251	TUBE
2	SW D 226N	SW226N	TO-252	REEL

Absolute maximum ratings

Symbol	Parameter	Value		Unit
		TO-251	TO-252	
$V_{DSS}$	Drain to source voltage	600		V
$I_D$	Continuous drain current (@ $T_C=25^{\circ}C$ )	4.0*		A
	Continuous drain current (@ $T_C=100^{\circ}C$ )	2.2*		A
$I_{DM}$	Drain current pulsed (note 1)	16		A
$V_{GS}$	Gate to source voltage	$\pm 30$		V
$E_{AS}$	Single pulsed avalanche energy (note 2)	310		mJ
$E_{AR}$	Repetitive avalanche energy (note 1)	20.4		mJ
dv/dt	Peak diode recovery dv/dt (note 3)	4.5		V/ns
$P_D$	Total power dissipation (@ $T_C=25^{\circ}C$ )	60	60	W
	Derating factor above 25°C	0.47	0.47	W/°C
$T_{STG}, T_J$	Operating junction temperature & storage temperature	-55 ~ + 150		°C
$T_L$	Maximum lead temperature for soldering purpose, 1/8 from case for 5 seconds.	300		°C

\*. Drain current is limited by junction temperature.

Thermal characteristics

Symbol	Parameter	Value		Unit
		TO-251	TO-252	
$R_{thjc}$	Thermal resistance, Junction to case	2.1	2.1	°C/W
$R_{thja}$	Thermal resistance, Junction to ambient	100		°C/W

Electrical characteristic (  $T_C = 25^\circ\text{C}$  unless otherwise specified )

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
<b>Off characteristics</b>						
$BV_{DSS}$	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	600			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$ , referenced to $25^\circ\text{C}$		0.59		$V/^\circ\text{C}$
$I_{DSS}$	Drain to source leakage current	$V_{DS}=600V, V_{GS}=0V$			1	$\mu A$
		$V_{DS}=480V, T_C=125^\circ\text{C}$			10	$\mu A$
$I_{GSS}$	Gate to source leakage current, forward	$V_{GS}=30V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-30V, V_{DS}=0V$			-100	nA
<b>On characteristics</b>						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2		4	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D=2A$		1.83	2.3	$\Omega$
$G_{fs}$	Forward transconductance	$V_{DS}=40V, I_D=2A$		3.5		S
<b>Dynamic characteristics</b>						
$C_{iss}$	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		571		pF
$C_{oss}$	Output capacitance			70		
$C_{rss}$	Reverse transfer capacitance			18		
$t_{d(on)}$	Turn on delay time	$V_{DS}=300V, I_D=4A, V_{GS}=10V, R_G=25\Omega$ (note 4 , 5)		12		ns
$t_r$	Rising time			27		
$t_{d(off)}$	Turn off delay time			110		
$t_f$	Fall time			41		
$Q_g$	Total gate charge	$V_{DS}=480V, V_{GS}=10V, I_D=4A$ , (note 4,5)		30		nC
$Q_{gs}$	Gate-source charge			3.8		
$Q_{gd}$	Gate-drain charge			13.8		

## Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			4	A
$I_{SM}$	Pulsed source current				16	A
$V_{SD}$	Diode forward voltage drop.	$I_S=4A, V_{GS}=0V$			1.4	V
$t_{rr}$	Reverse recovery time	$I_S=4A, V_{GS}=0V$ , $di_f/dt=100A/\mu s$		337		ns
$Q_{rr}$	Reverse recovery charge			2.25		$\mu C$

※. Notes

1. Repeattive rating : pulse width limited by junction temperature.
2.  $L = 38\text{mH}$ ,  $I_{AS} = 4A$ ,  $V_{DD} = 50V$ ,  $R_G=25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 4A$ ,  $di/dt = 100A/\mu s$ ,  $V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ .
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

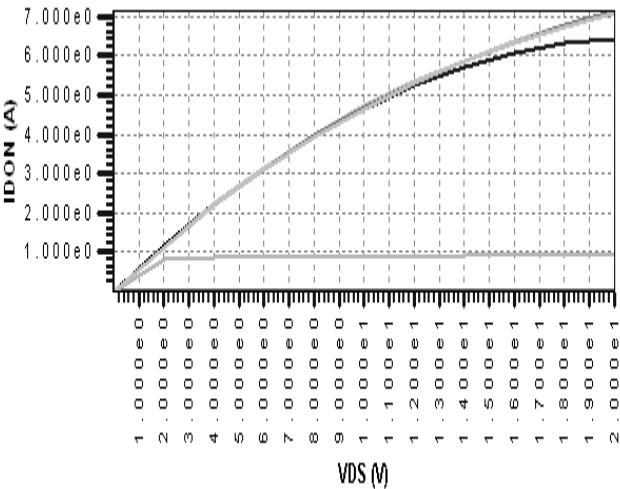


Fig. 2. On-resistance variation vs. drain current and gate voltage

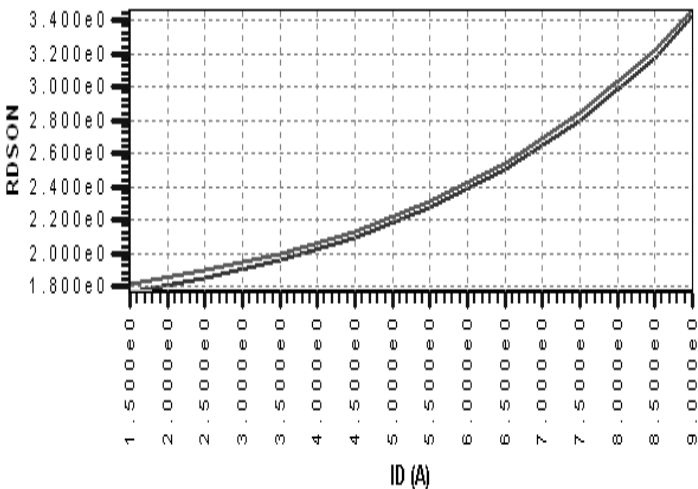


Fig. 3. Gate charge characteristics

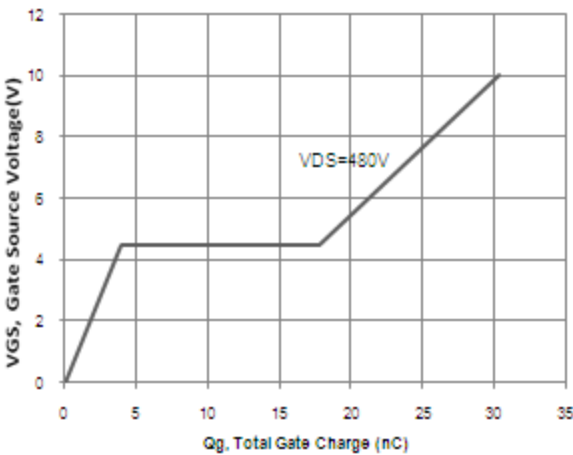


Fig. 4. On state current vs. diode forward voltage

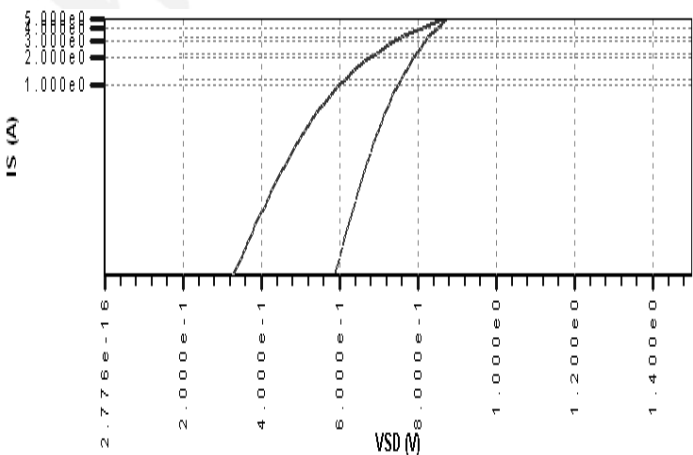


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

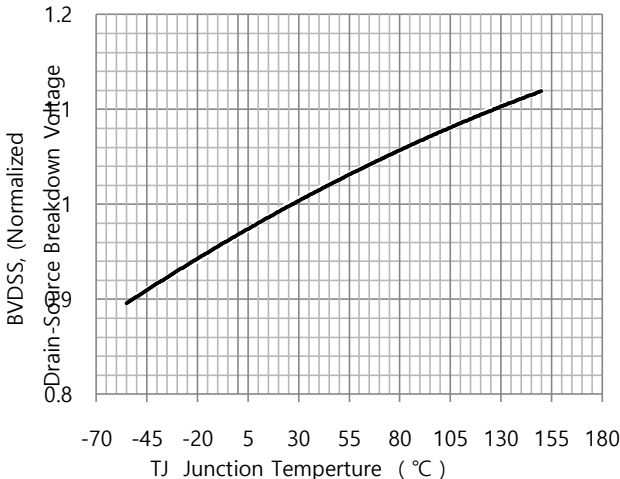


Fig. 6. On resistance variation vs. junction temperature

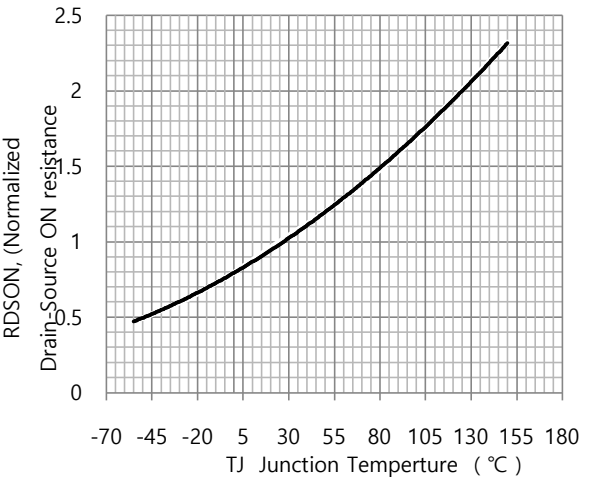


Fig. 7. Maximum safe operating area

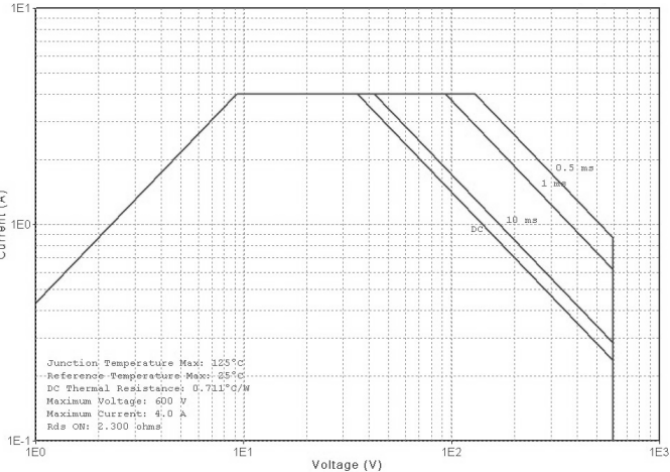


Fig. 8. Transient thermal response curve

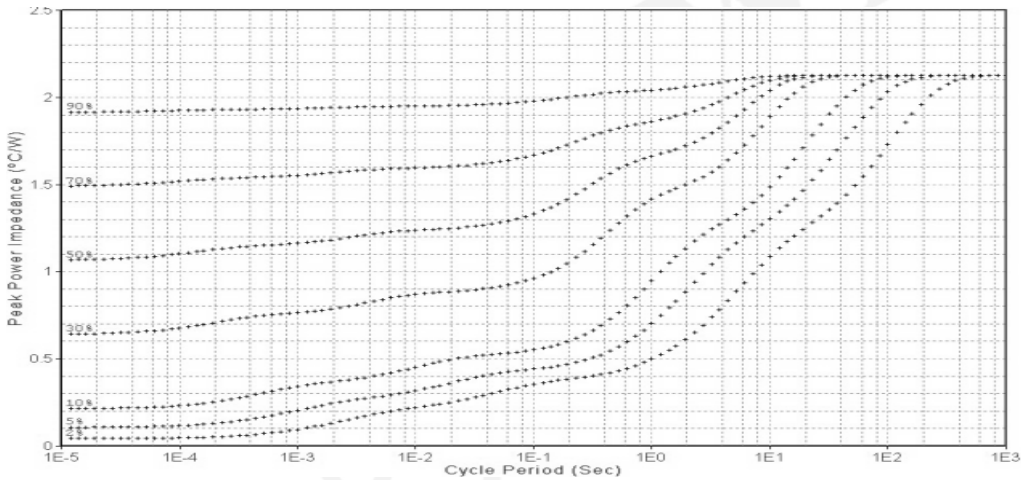


Fig. 9. Gate charge test circuit & waveform

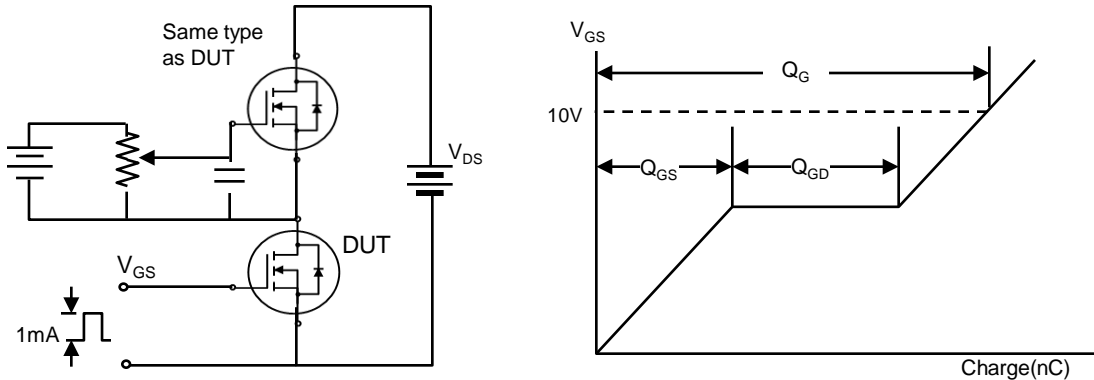


Fig. 10. Switching time test circuit & waveform

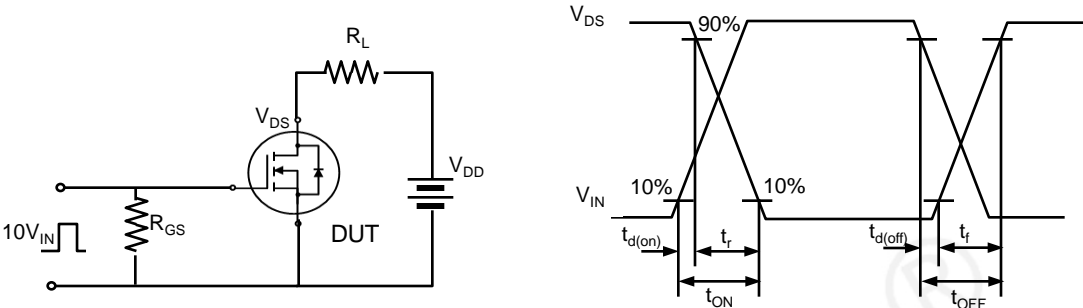


Fig. 11. Unclamped Inductive switching test circuit & waveform

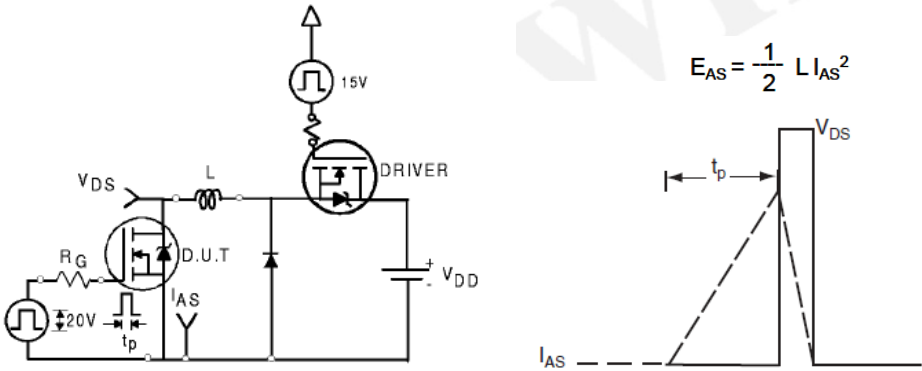
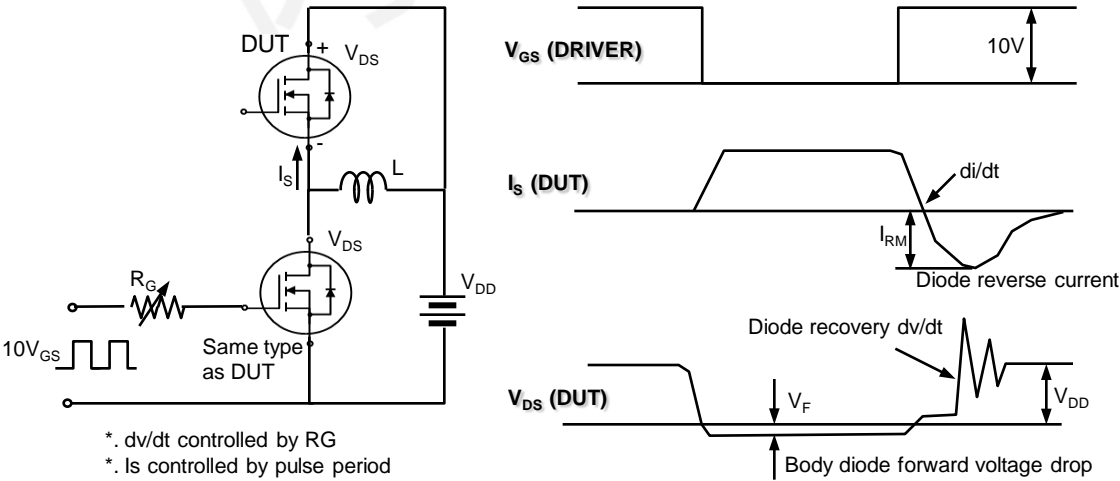



Fig. 12. Peak diode recovery dv/dt test circuit & waveform



Samwin®  
内部保密

### DISCLAIMER

- \* All the data&curve in this document was tested in XI'AN SEMIPOWER TESTING & APPLICATION CENTER.
- \* This product has passed the PCT,TC,HTRB,HTGB,HAST,PC and Solderdunk reliability testing.
- \* Qualification standards can also be found on the Web site (<http://www.semipower.com.cn>) 
- \* Suggestions for improvement are appreciated, Please send your suggestions to [samwin@samwinsemi.com](mailto:samwin@samwinsemi.com)